

REMARKS

The Examiner has rejected claim 1 pursuant to 35 U.S.C. §102(e) as anticipated by the disclosure of United States Patent No. 6,930,336. According to the Examiner, United States Patent No. 6,930,336 discloses a CMOS image sensor comprising (among other things) “a first doped charge collecting region 46 buried within the p-type doped region and configured to operate as a depleted potential well.”

This rejection is respectfully traversed. As demonstrated by the accompanying Declaration of Richard B. Merrill, the inventor of both the subject matter claimed in claim 1 of the above-identified patent application and the subject matter disclosed and claimed in United States Patent No. 6,930,336, this reference does not disclose or suggest an image sensor including “a first doped charge collecting region 46 buried within the p-type doped region and configured to operate as a depleted potential well.” According to the Merrill Declaration, in order to operate as asserted by the Examiner, the image sensor disclosed in United States Patent No. 6,930,336 would have to be modified in a manner that would seriously degrade its operation, and, because of the seriously degraded operation, no person of ordinary skill in the art would make any such modification.

The Examiner has also rejected claim 1 pursuant to 35 U.S.C. §102(b) as anticipated by the portion of the disclosure in the above-identified patent application

which constitutes admitted prior art, namely the disclosure related to FIG. 1 of the above-identified patent application. According to the Examiner, the admitted prior art discloses a CMOS image sensor comprising (among other things) "a first doped charge collecting region 103 buried within the p-type doped region and configured to operate as a depleted potential well."

This rejection is also respectfully traversed. As demonstrated by the accompanying Declaration of Richard B. Merrill, the inventor of both the subject matter claimed in claim 1 of the above-identified patent application and the subject matter disclosed in the admitted prior art description contained in the above-identified patent application, the admitted prior art does not disclose or suggest an image sensor including "a first doped charge collecting region 103 buried within the p-type doped region and configured to operate as a depleted potential well."

If the Examiner has any questions regarding this application or this response, the Examiner is requested to telephone the undersigned at 775-586-9500.

Respectfully submitted,  
SIERRA PATENT GROUP, LTD.

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Jonathan Hanish  
Reg. No.: 57, 821

Sierra Patent Group, Ltd.  
1657 Hwy 395, Suite 202  
Minden, NV 89423  
(775) 586-9500